

AMENDMENTS TO THE CLAIMS

Claim 1. (Canceled)

2. (Currently Amended) ~~The method of claim 1,~~ A method comprising:
forming a first conductive material in an opening through a dielectric to a contact
point; and
forming a second conductive material on the first conductive material,
wherein the first conductive material comprises a unidirectional electrical
conductivity and the unidirectional conductivity is configured to be in a direction
corresponding to a projection to or from the contact point and the second conductive
material, and wherein forming the second conductive material comprises introducing a
seed material into the via in a manner that leaves the first conductive material overlying
the contact point.

Claims 3 - 5. (Canceled)

6. (Currently Amended) ~~The method of claim 5, further comprising:~~ A method
comprising:
forming a first conductive material in an opening through a dielectric to a contact
point; and
forming a second conductive material on the first conductive material;
forming an interconnect structure in the opening on the second conductive
material;
prior to forming ~~a~~ the third conductive material, modifying the exposed surface
of the interconnect structure, wherein modifying the surface of the interconnect
structure comprises one of stripping with a stripping agent, planarizing, polishing, and
doping with a dopant;
forming the third conductive material on an exposed portion of the interconnect
structure,
wherein the first conductive material comprises a unidirectional electrical
conductivity and the unidirectional conductivity is configured to be in a direction
corresponding to a projection to or from the contact point and the second conductive

material, and wherein the third conductive material comprises a unidirectional electrical conductivity in a direction normal to the exposed portion of the interconnect structure.

7. (Currently Amended) ~~The method of claim 1,~~ A method comprising:
forming a first conductive material in an opening through a dielectric to a contact point; and
forming a second conductive material on the first conductive material,
wherein the first conductive material comprises a unidirectional electrical conductivity and the unidirectional conductivity is configured to be in a direction corresponding to a projection to or from the contact point and the second conductive material, and wherein forming the first conductive material comprises deposition via one of electroplating, chemical vapor deposition, sputter deposition, molecular beam deposition, and gel separation in an electronic field.

Claims 8 - 9. (Canceled)

10. (Currently Amended) ~~The method of claim 1,~~ A method comprising:
forming a first conductive material in an opening through a dielectric to a contact point; and
forming a second conductive material on the first conductive material,
wherein the first conductive material comprises a unidirectional electrical conductivity and the unidirectional conductivity is configured to be in a direction corresponding to a projection to or from the contact point and the second conductive material, and wherein forming the first conductive material includes forming a layer of material comprising a property tending to reduce metal diffusion between the second conductive material and the dielectric.

11. (Currently Amended) ~~The method of claim 1,~~ A method comprising:
forming a first conductive material in an opening through a dielectric to a contact point; and
forming a second conductive material on the first conductive material,
wherein the first conductive material comprises a unidirectional electrical conductivity and the unidirectional conductivity is configured to be in a direction corresponding to a projection to or from the contact point and the second conductive

material, and wherein forming the first conductive material includes forming a layer of material comprising a property tending to reduce electron migration between the second conductive material and the dielectric.

12. (Currently Amended) ~~The method of claim 1, A method comprising:~~
forming a first conductive material in an opening through a dielectric to a contact point; and

forming a second conductive material on the first conductive material,
wherein the first conductive material comprises a unidirectional electrical conductivity and the unidirectional conductivity is configured to be in a direction corresponding to a projection to or from the contact point and the second conductive material, and wherein forming the first conductive material includes forming a layer of material comprising a property tending to act as an etch stop layer.

13. (Currently Amended) ~~The method of claim 1, further comprising A method comprising:~~

forming a first conductive material in an opening through a dielectric to a contact point;

chemically-mechanically polishing the first conductive material with a polishing slurry;

forming a second conductive material on the first conductive material,
wherein the first conductive material comprises a unidirectional electrical conductivity and the unidirectional conductivity is configured to be in a direction corresponding to a projection to or from the contact point and the second conductive material.

14. (Currently Amended) ~~The method of claim 1, further comprising A method comprising:~~

forming a first conductive material in an opening through a dielectric to a contact point;

doping the first conductive material;

forming a second conductive material on the first conductive material.

wherein the first conductive material comprises a unidirectional electrical conductivity and the unidirectional conductivity is configured to be in a direction corresponding to a projection to or from the contact point and the second conductive material.

Claims 15 – 26. (Cancelled)